



First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/719,772	
Filing Date	November 21, 2003	
Group Art Unit	2815	
Examiner Name	Unknown <i>Ferty</i>	
Confirmation No.	2908 <i>2825-12908</i>	
Attorney Docket No.	400.252US01	
Title: APPARATUS AND METHOD FOR SPLIT GATE NROM MEMORY		Sheet 1 of 7

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Examiner Signature	<i>David Ferty</i>	Date Considered	<i>9/24/4</i>
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